

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

10-13. (Cancelled)

14. (Currently Amended) The production method according to Claim 10, A  
method for producing a bonding wafer by the hydrogen ion delamination method, comprising  
in order;

bonding a base wafer and a bond wafer having a micro bubble layer formed by  
gas ion implantation;

delaminating the base wafer and the bond wafer at the micro bubble layer as a  
border;

forming an oxide film by subjecting the wafer to bonding heat treatment in an  
oxidizing atmosphere;

masking at least portions of a top surface other than a peripheral portion to be  
removed; and

removing the peripheral portion of a thin film formed on the base wafer after  
the delamination step, wherein the removal of the peripheral portion of the thin film is  
attained by etching the wafer, with masking at least portions of the top surface other than the  
peripheral portion to be removed.

15. (Currently Amended) The production method according to Claim 12, Claim  
14, wherein the removal of the peripheral portion of the thin film is attained by removing a  
region of 1-5 mm from the peripheral end of the base wafer, the removal of the peripheral  
portion of the thin film is attained by etching the wafer with masking at least portions of the  
top surface other than the peripheral portion to be removed.

16. (Currently Amended) The production method according to Claim 13, Claim 14, wherein the thin film has at least an SOI layer, and the removal of the peripheral portion of the thin film is attained by removing at least the SOI layer for a region of 1-5 mm from the peripheral end of the base wafer. the removal of the peripheral portion of the thin film is attained by etching the wafer with masking at least portions of the top surface other than the peripheral portion to be removed.

17. (Currently Amended) The production method according to Claim 10A method for producing a bonding wafer by the hydrogen ion delamination method comprising at least a step of bonding a base wafer and a bond wafer having a micro bubble layer formed by gas ion implantation and a step of delaminating them at the micro bubble layer as a border, wherein a peripheral portion of a thin film formed on the base wafer is removed after the delamination step, and the removal of the peripheral portion of the thin film is attained by holding together a plurality of wafers stacked so that at least the peripheral portions to be removed should be exposed, and etching them.

18. (Currently Amended) The production method according to Claim 12\_17, wherein the removal of the peripheral portion of the thin film is attained by removing a region of 1-5 mm from the peripheral end of the base wafer. the removal of the peripheral portion of the thin film is attained by holding together a plurality of wafers stacked so that at least the peripheral portions to be removed should be exposed, and etching them.

19. (Currently Amended) The production method according to Claim 13 Claim 17 wherein the thin film has at least an SOI layer, and the removal of the peripheral portion of the thin film is attained by removing at least the SOI layer for a region of 1-5 mm from the peripheral end of the base wafer. wherein the removal of the peripheral portion of the thin film is attained by holding together a plurality of wafers stacked so that at least the peripheral portions to be removed should be exposed, and etching them.

20. (Currently Amended) The production method according to Claim 10A method for producing a bonding wafer by the hydrogen ion delamination method comprising at least a step of bonding a base wafer and a bond wafer having a micro bubble layer formed by gas ion implantation and a step of delaminating them at the micro bubble layer as a border, wherein a peripheral portion of a thin film formed on the base wafer is removed after the delamination step, and, wherein the removal of the peripheral portion of the thin film is attained by polishing only the peripheral portion while supplying pure water to the center of the wafer.

21. (Currently Amended) The production method according to Claim 12Claim 20, wherein the removal of the peripheral portion of the thin film is attained by removing a region of 1-5 mm from the peripheral end of the base wafer. the removal of the peripheral portion of the thin film is attained by polishing only the peripheral portion.

22. (Currently Amended) The production method according to Claim 13Claim 20, wherein the thin film has at least an SOI layer, and the removal of the peripheral portion of the thin film is attained by removing at least the SOI layer for a region of 1-5 mm from the peripheral end of the base wafer. the removal of the peripheral portion of the thin film is attained by polishing only the peripheral portion.

23-24. (Cancelled)